

TSD50R550S1/TSU50R550S1

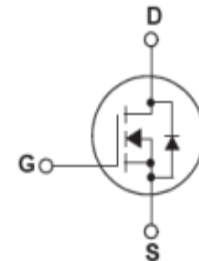
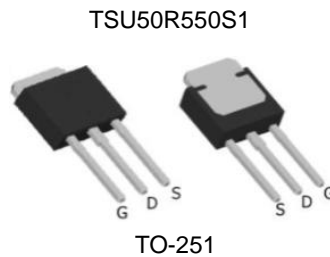
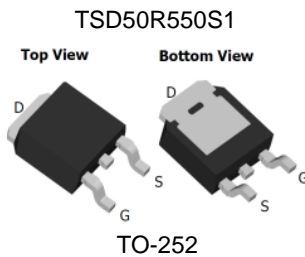
500V 7.6A N-Channel SJ-MOSFET

General Description

Truesemi SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance. This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. SJ-FET is suitable for various AC/DC power conversion in switching mode operation for higher efficiency.

Features

- 550V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 0.48\Omega$
- Ultra Low gate charge (typ. $Q_g = 25\text{nC}$)
- 100% avalanche tested



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	500	V
I_D	Drain Current -Continuous ($T_C = 25^\circ\text{C}$) -Continuous ($T_C = 100^\circ\text{C}$)	7.6 5	A
I_{DM}	Drain Current – Pulsed (Note 1)	18	A
V_{GSS}	Gate-Source voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	86	mJ
I_{AR}	Avalanche Current (Note 1)	1.7	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	0.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	15	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) -Derate above 25°C	57 0.8	W W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.0	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	$^\circ\text{C/W}$

Electrical Characteristics TC = 25 °C unless otherwise noted

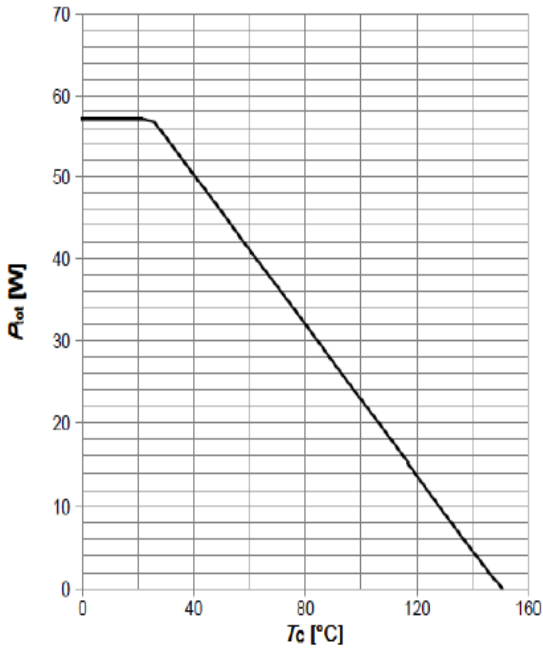
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25 °C	500	--	--	V
		V _{GS} = 0V, I _D = 250μA, T _J = 150 °C	--	550	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25 °C	--	0.6	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} = 0V -T _C = 150 °C	--	-- 10	1 --	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.5	3.5	4.5	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 3.5A	--	0.48	0.55	Ω
g _{FS}	Forward Trans conductance	V _{DS} = 40V, I _D = 3.5A (Note 4)	--	16	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 100V, V _{GS} = 0V, f = 1.0MHz	--	380	--	pF
C _{oss}	Output Capacitance		--	110	--	pF
C _{rss}	Reverse Transfer Capacitance		--	7	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 400V, I _D = 3.5A R _G = 20Ω(Note 4, 5)	--	13	--	ns
t _r	Turn-On Rise Time		--	10	--	ns
t _{d(off)}	Turn-Off Delay Time		--	85	--	ns
t _f	Turn-Off Fall Time		--	14	--	ns
Q _g	Total Gate Charge	V _{DS} = 480V, I _D = 3.5A V _{GS} = 10V (Note 4, 5)	--	25	--	nC
Q _{gs}	Gate-Source Charge		--	2.0	--	nC
Q _{gd}	Gate-Drain Charge		--	2.7	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	7	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	18	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _F = 3.5A	--	0.9	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _F = 3.5A di _F /dt = 100A/μs (Note 4)	--	190	--	ns
Q _{rr}	Reverse Recovery Charge		--	2.3	--	μC

NOTES:

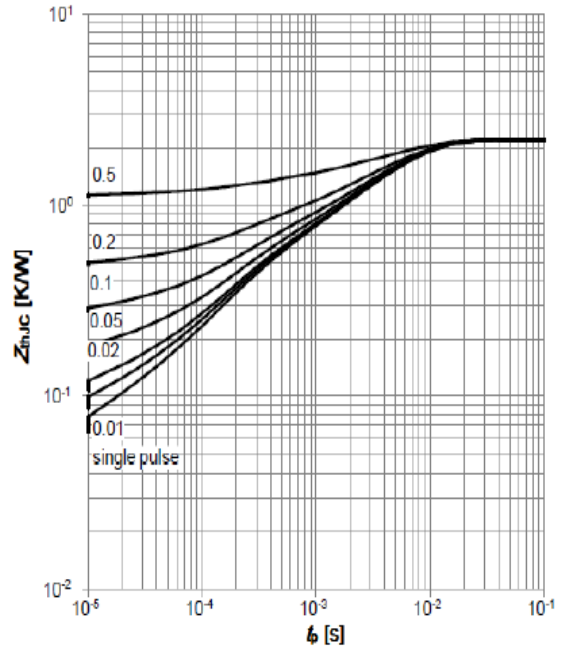
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 60mH, I_{AS} = 1.7A, V_{DD} = 50V, Starting T_J = 25 °C
3. I_{SD} ≤ 7A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25 °C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

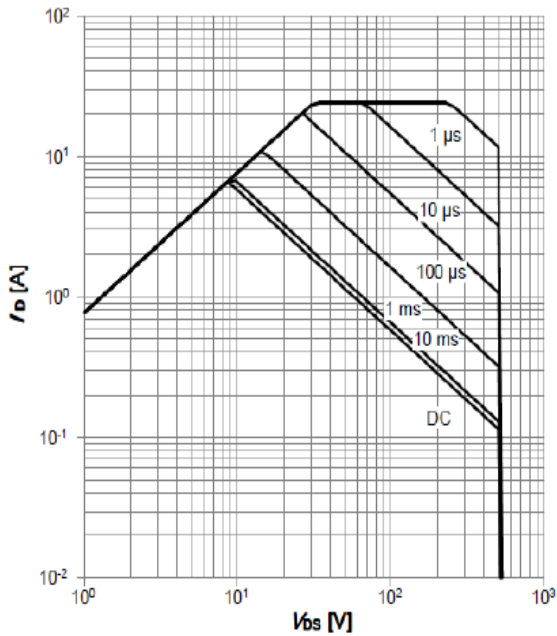
Power dissipation



Max. transient thermal impedance

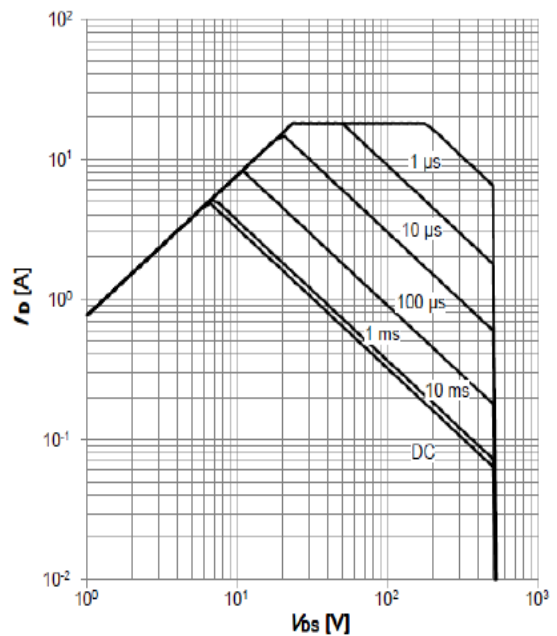


Safe operating area $T_C=25^\circ\text{C}$



$I_D=f(V_{DS}); T_C=25^\circ\text{C}; V_{GS} > 7V;$
 $D=0;$ parameter t_p

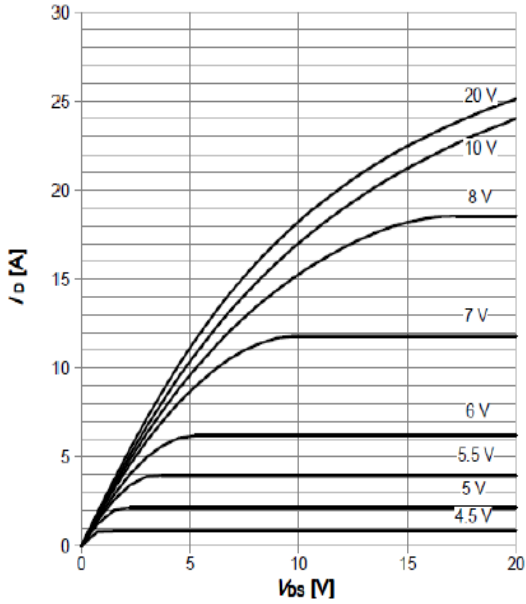
Safe operating area $T_C=80^\circ\text{C}$



$I_D=f(V_{DS}); T_C=80^\circ\text{C}; V_{GS} > 7V;$
 $D=0;$ parameter t_p

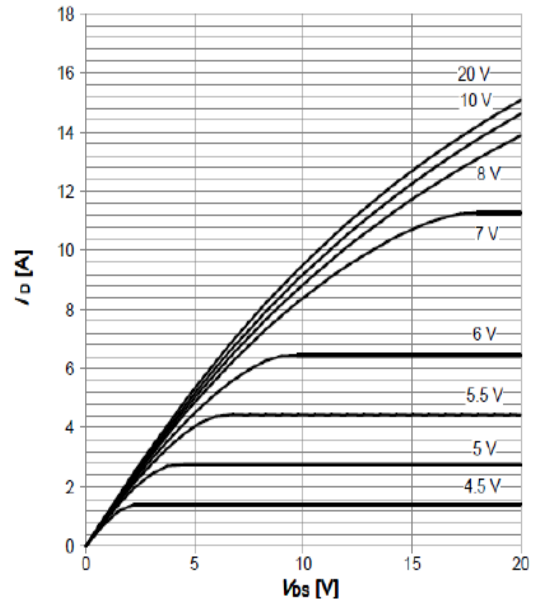
Typical Performance Characteristics

Typ. output characteristic



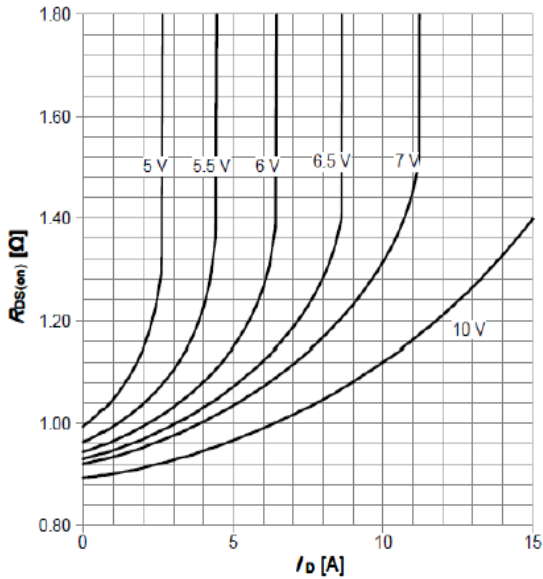
$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C};$
parameter $t_p=10\mu\text{s}, V_{GS}$

Typ. output characteristic



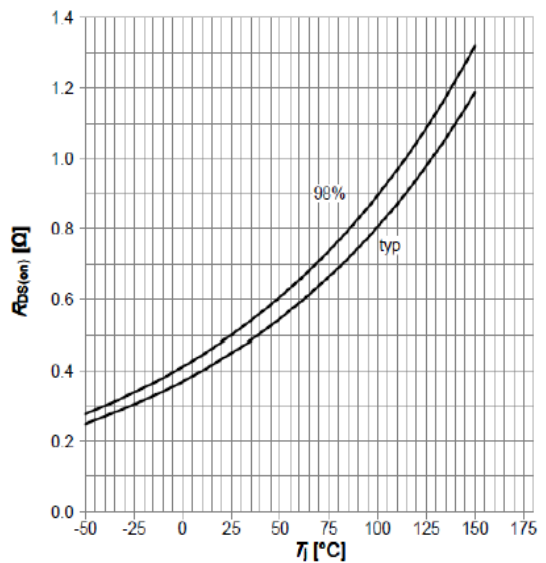
$I_D=f(V_{DS}); T_j=125\text{ }^\circ\text{C};$
parameter $t_p=10\mu\text{s}, V_{GS}$

Typ. Drain-Source on resistance



$R_{Dson}=f(I_D); T_j=125\text{ }^\circ\text{C};$ parameter V_{GS}

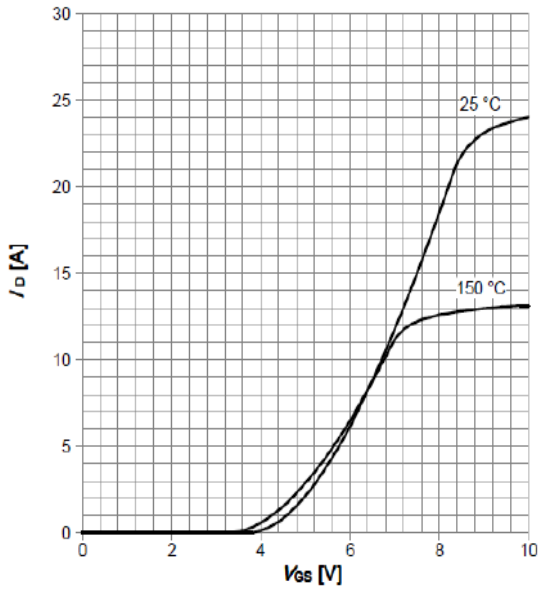
Typ. Drain-Source on resistance



$R_{Dson}=f(T_j); T_j=125\text{ }^\circ\text{C};$ parameter $I_D=2.3\text{A } V_{GS}=13\text{V}$

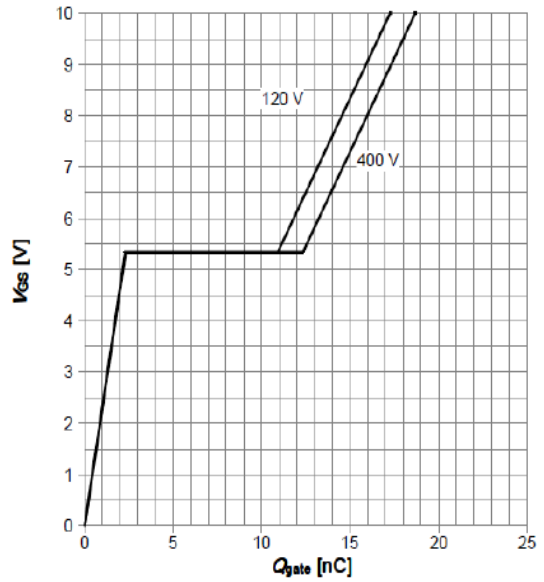
Typical Performance Characteristics

Typ. Transfer characteristic



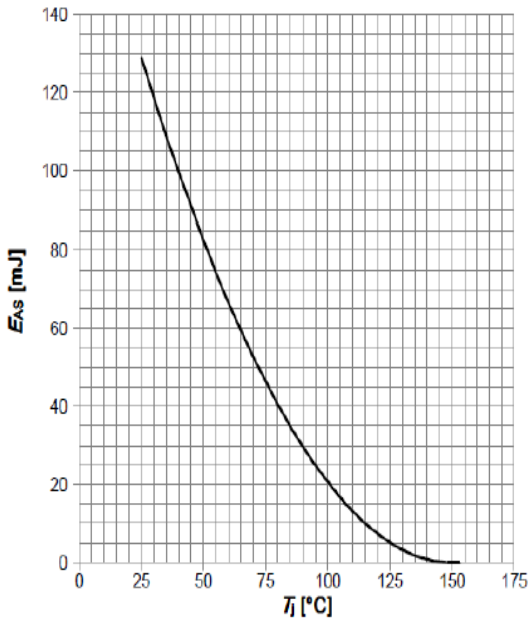
$I_D = f(V_{DS}); V_{DS} > 20V$;
parameter $t_p = 10\mu s$,

Typ. gate charge



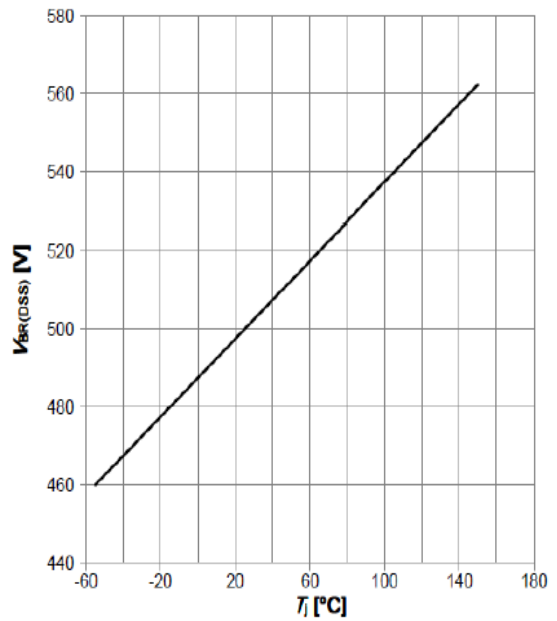
$V_{GS} = f(Q_g), I_D = 2.9 A$ pulsed

Avalanche energy



$E_{AS} = f(T_j); I_D = 2.9 A; V_{DD} = 50 V$

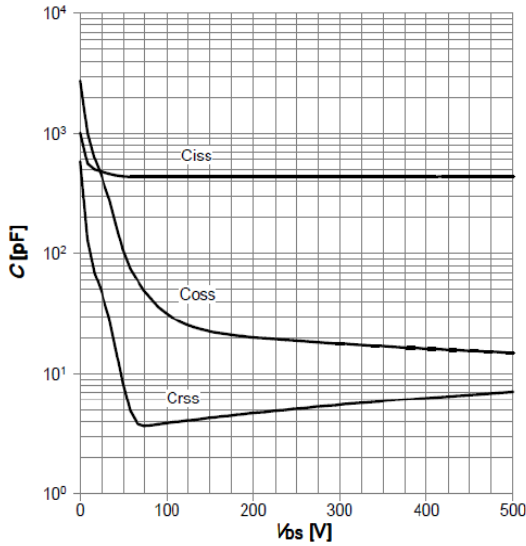
Drain-source breakdown voltage



$V_{BR(DSS)} = f(T_j); I_D = 1 mA$

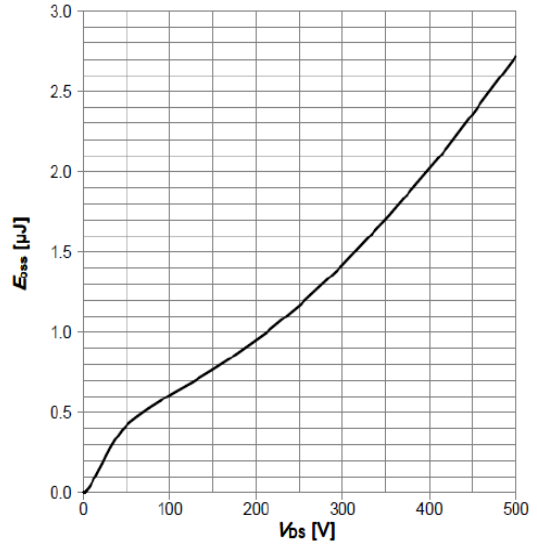
Typical Performance Characteristics

Typ. capacitances



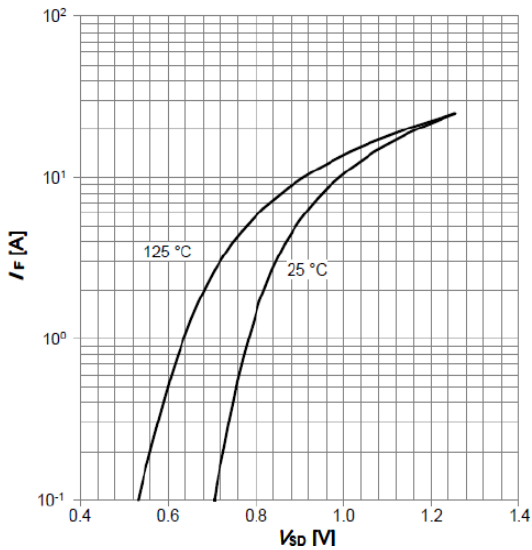
$$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$$

Typ. C_{oss} stored energy



$$E_{OSS}=f(V_{DS})$$

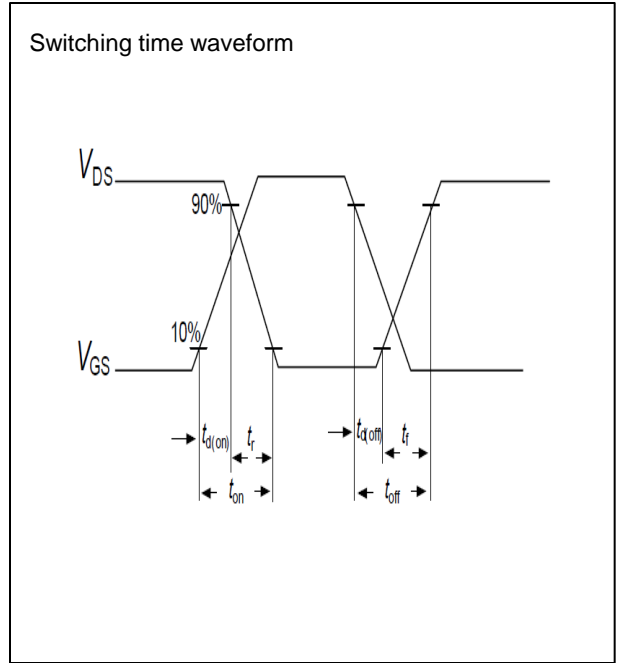
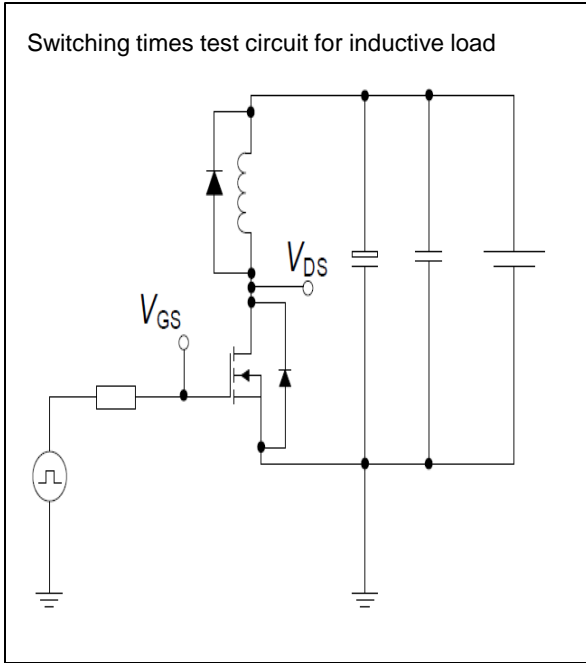
Forward characteristics of reverse diode



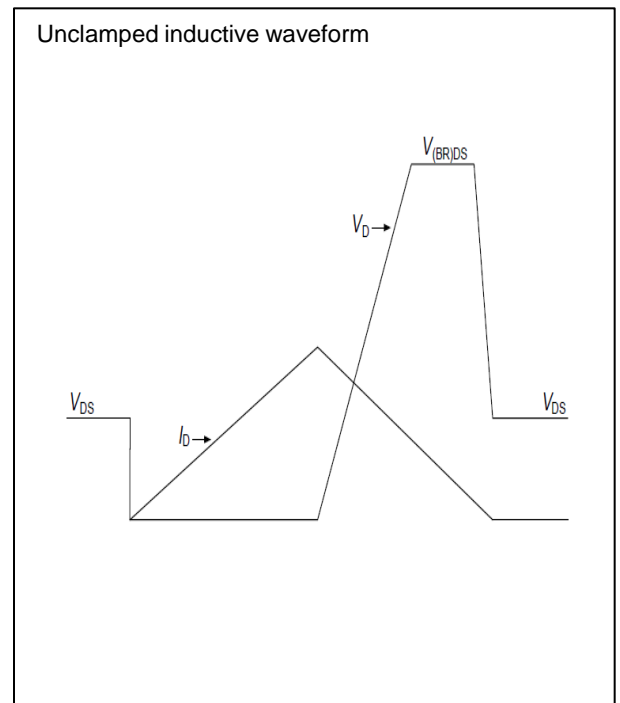
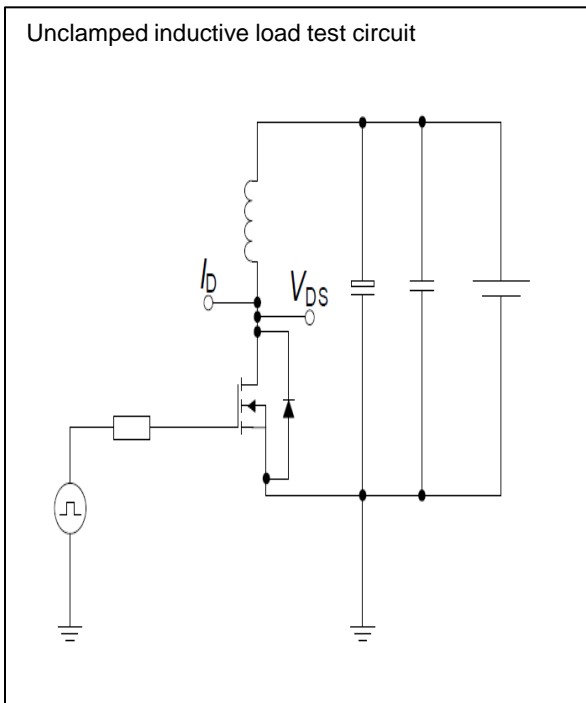
$$I_F=f(V_{SD}); \text{parameter: } T_j$$

Test circuits

Switching times test circuit and waveform for inductive load

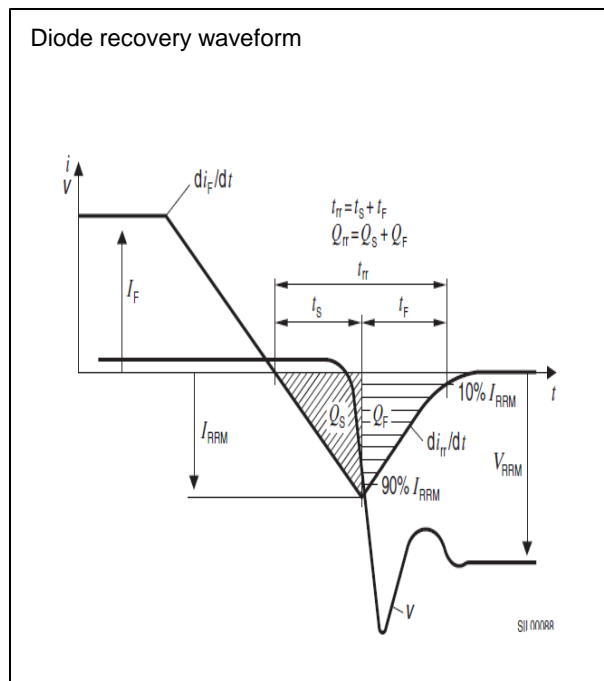
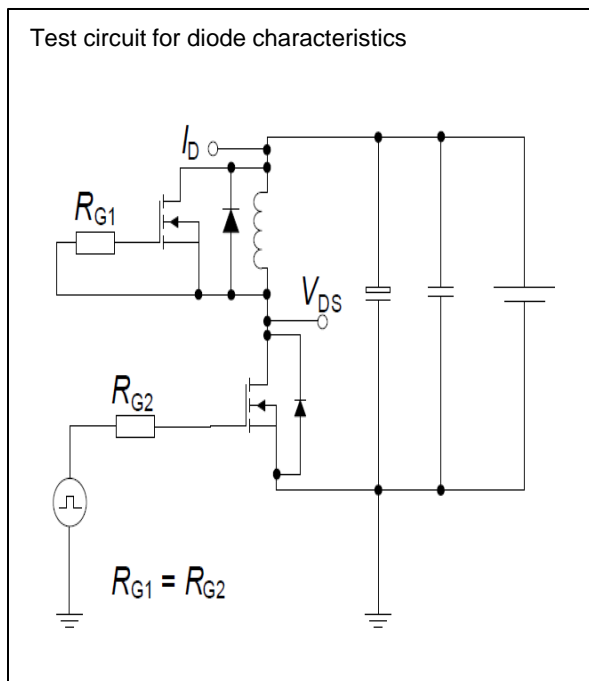


Unclamped inductive load test circuit and waveform



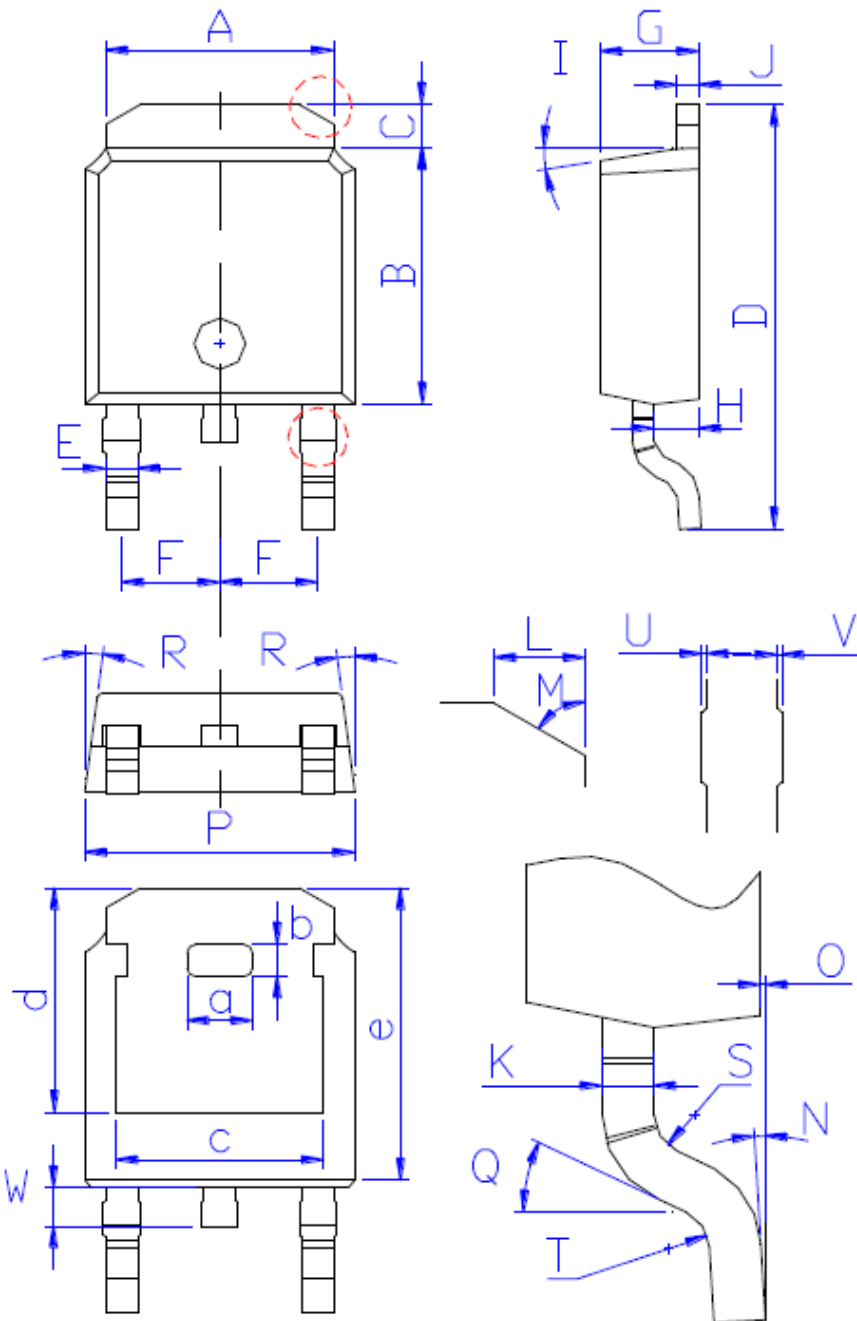
Test circuits

Test circuit and waveform for diode characteristics



Package Outline TO-252

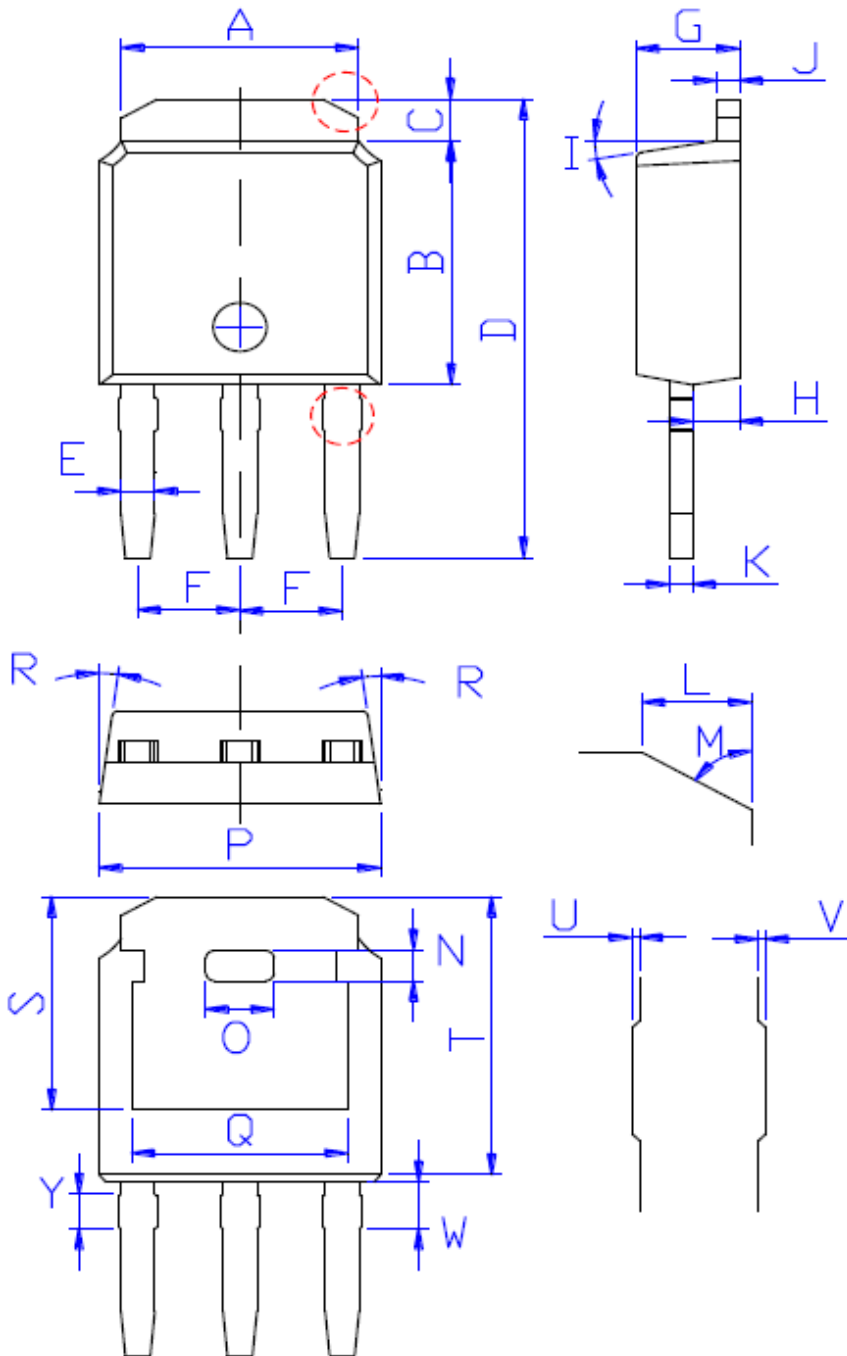
TSD50R550S1/TSU50R550S1 500V 7.6A N-Channel SJ-MOSFET



DIM	MILLIMETERS
A	5.34 ± 0.30
B	6.00 ± 0.30
C	1.05 ± 0.30
D	9.95 ± 0.30
E	0.76 ± 0.15
F	2.28 ± 0.15
G	2.30 ± 0.30
H	1.06 ± 0.30
I	$(4-10)^\circ$
J	0.51 ± 0.15
K	0.52 ± 0.15
L	0.80 ± 0.30
M	60°
N	$(0-10)^\circ$
O	0.05 ± 0.05
P	6.60 ± 0.30
Q	25°
R	$(4-8.5)^\circ$
S	R0.40
T	R0.40
U	0.05 ± 0.05
V	0.05 ± 0.05
W	0.90 ± 0.30
a	1.80 ± 0.30
b	0.75 ± 0.30
c	4.85 ± 0.30
d	5.30 ± 0.30
e	6.90 ± 0.30

Package Outline TO-251

TSD50R550S1/TSU50R550S1 500V 7.6A N-Channel SJ-MOSFET



DIM	MILLIMETERS
A	5.34±0.30
B	6.00±0.30
C	1.05±0.30
D	11.31±0.30
E	0.76±0.15
F	2.28±0.15
G	2.30±0.30
H	1.06±0.30
I	(4-10)°
J	0.51±0.15
K	0.52±0.15
L	0.80±0.30
M	60°
N	0.75±0.30
O	1.80±0.30
P	6.60±0.30
Q	4.85±0.30
R	(4-8.5)°
S	5.30±0.30
T	6.90±0.30
U	0.05±0.05
V	0.05±0.05
W	1.15±0.25
Y	0.85±0.25